Power MOSFET 200 mA, 50 V

N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low Threshold Voltage (V_{GS(th)}: 0.5 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb-Free Packages are Available

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current - Continuous @ $T_A = 25$ °C - Pulsed Drain Current $(t_p \le 10 \mu s)$	I _D I _{DM}	200 800	mA
Total Power Dissipation @ T _A = 25°C	P _D	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

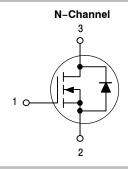
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com

200 mA, 50 V $R_{DS(on)} = 3.5 Ω$





SOT-23 CASE 318 STYLE 21



MARKING

J1 = Device Code M = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138LT1	SOT-23	3000 Tape & Reel
BSS138LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
BSS138LT3	SOT-23	10,000 Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

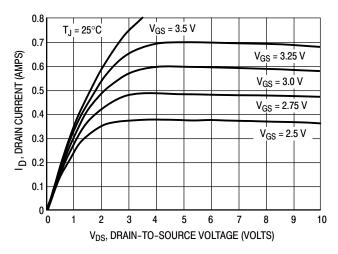
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Char	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc)		V _{(BR)DSS}	50	-	_	Vdc	
Zero Gate Voltage Drain Current $ \begin{array}{l} (V_{DS}=25~\text{Vdc},~V_{GS}=0~\text{Vdc},~25^{\circ}\text{C})\\ (V_{DS}=50~\text{Vdc},~V_{GS}=0~\text{Vdc},~25^{\circ}\text{C})\\ (V_{DS}=50~\text{Vdc},~V_{GS}=0~\text{Vdc},~150^{\circ}\text{C}) \end{array} $		I _{DSS}	- - -	- - -	0.1 0.5 5.0	μAdc	
Gate-Source Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	-	-	±0.1	μAdc	
ON CHARACTERISTICS (Note 1)							
Gate–Source Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$		V _{GS(th)}	0.5	-	1.5	Vdc	
Static Drain-to-Source On-Resistance $ \begin{array}{l} (V_{GS}=2.75~Vdc,~I_D<200~mAdc,~T_A=-40^{\circ}C~to~+85^{\circ}C)\\ (V_{GS}=5.0~Vdc,~I_D=200~mAdc) \end{array} $		r _{DS(on)}	- -	5.6 -	10 3.5	Ω	
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f = 1.0 kHz)		9fs	100	-	-	mmhos	
DYNAMIC CHARACTERISTICS							
Input Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{iss}	_	40	50	pF	
Output Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz) C _{oss} – 12		25				
Transfer Capacitance	$(V_{DG} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{rss}	_	3.5	5.0		
SWITCHING CHARACTERISTICS (N	ote 2)						
Turn-On Delay Time	0/ 20\/do - 02\/do\	t _{d(on)}	_	-	20	ns	
Turn-Off Delay Time	(V _{DD} = 30 Vdc, I _D = 0.2 Adc,)	t _{d(off)}	-	-	20		

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.

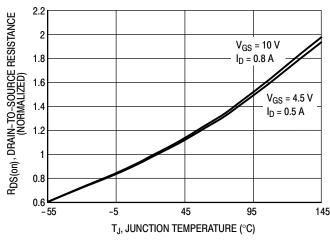
TYPICAL ELECTRICAL CHARACTERISTICS



0.9 25°C V_{DS} = 10 V 0.8 -55°C ID, DRAIN CURRENT (AMPS) 0.7 150°C 0.6 0.5 0.4 0.3 0.2 0.1 0.5 1.5 4.5 VGS, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



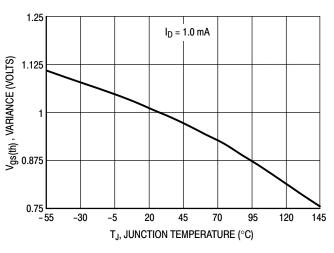
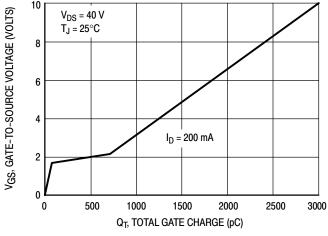


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature



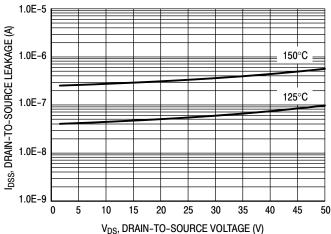
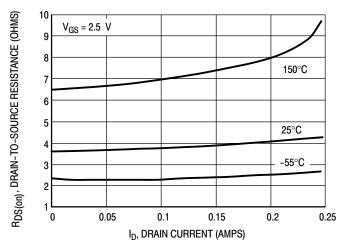


Figure 5. Gate Charge

Figure 6. IDSS

TYPICAL ELECTRICAL CHARACTERISTICS



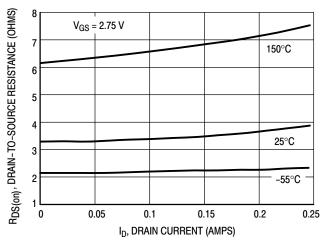
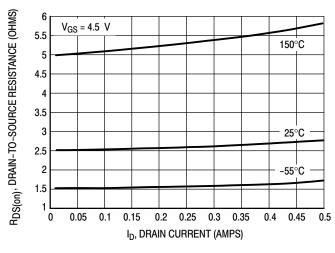


Figure 7. On-Resistance versus Drain Current

Figure 8. On-Resistance versus Drain Current



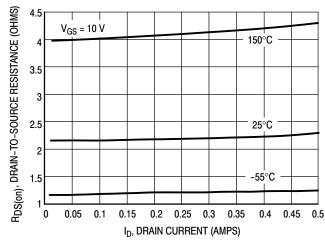
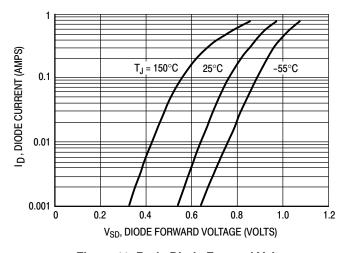


Figure 9. On-Resistance versus Drain Current

Figure 10. On-Resistance versus Drain Current



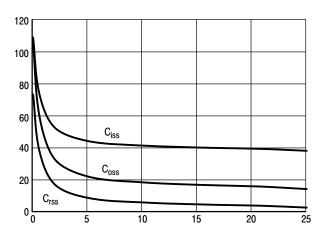
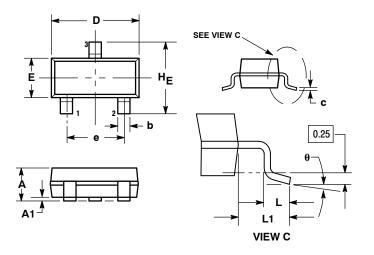


Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

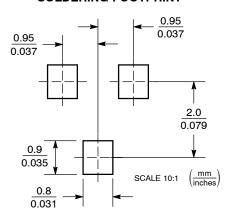
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 21: PIN 1. GATE 2. SOUR

SOURCE DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163. Denver. Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

BSS138LT1/D